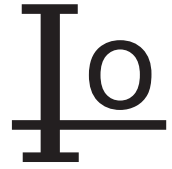


MMBTA42

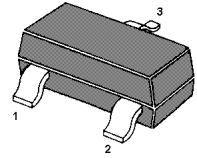
TRANSISTOR (NPN)



FEATURES

- High breakdown voltage
- Low collector-emitter saturation voltage
- Complementary to MMBTA92 (PNP)

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1. BASE
2. EMITTER
3. COLLECTOR

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CB0}	Collector-Base Voltage	300	V
V_{CE0}	Collector-Emitter Voltage	300	V
V_{EB0}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.3	A
P_C	Collector Power dissipation	0.35	W
$R_{\theta JA}$	Thermal Resistance, junction to Ambient	357	$^{\circ}\text{C}/\text{mW}$
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55to +150	$^{\circ}\text{C}$

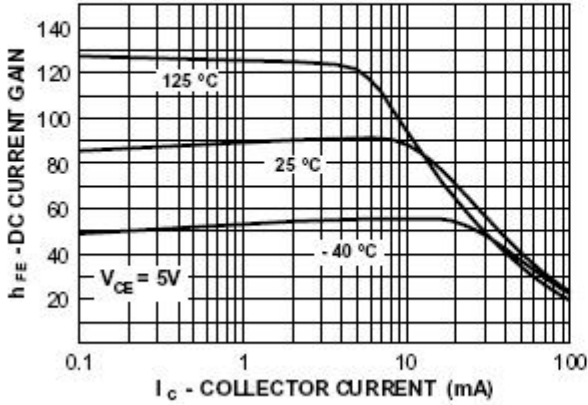
ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}$, $I_E=0$	300		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}$, $I_B=0$	300		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}$, $I_C=0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB}=200\text{V}$, $I_E=0$		0.25	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}$, $I_C=0$		0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=10\text{V}$, $I_C=1\text{mA}$	60		
	$h_{FE(2)}$	$V_{CE}=10\text{V}$, $I_C=10\text{mA}$	100	200	
	$h_{FE(3)}$	$V_{CE}=10\text{V}$, $I_C=30\text{mA}$	60		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=20\text{mA}$, $I_B=2\text{mA}$		0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=20\text{mA}$, $I_B=2\text{mA}$		0.9	V
Transition frequency	f_T	$V_{CE}=20\text{V}$, $I_C=10\text{mA}$, $f=30\text{MHz}$	50		MHz

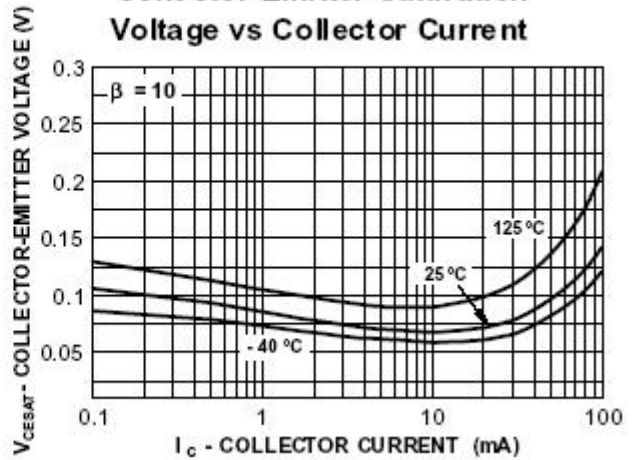
Typical Characteristics

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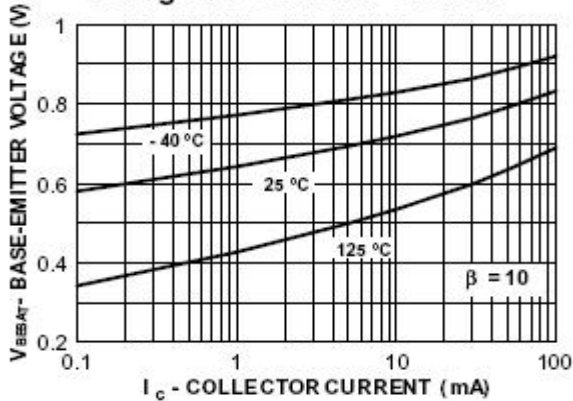
DC Current Gain vs Collector Current



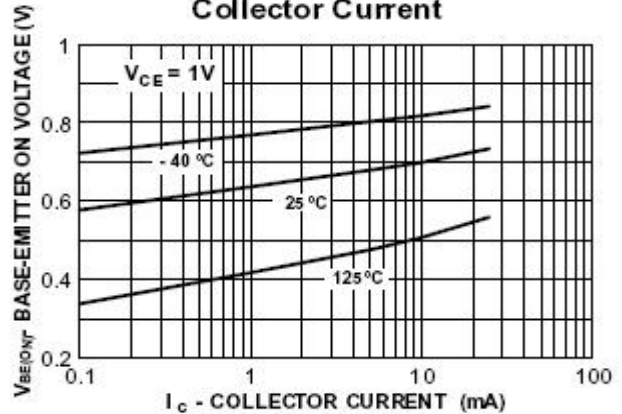
Collector-Emitter Saturation Voltage vs Collector Current



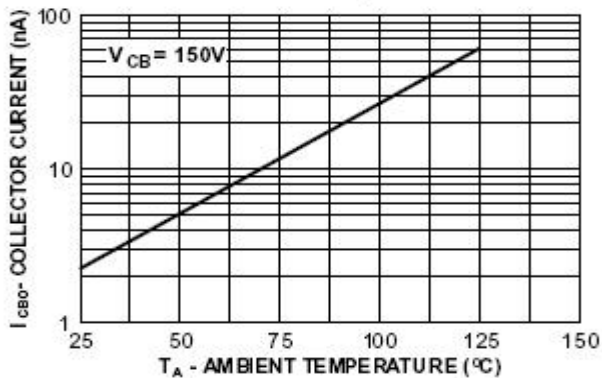
Base-Emitter Saturation Voltage vs Collector Current



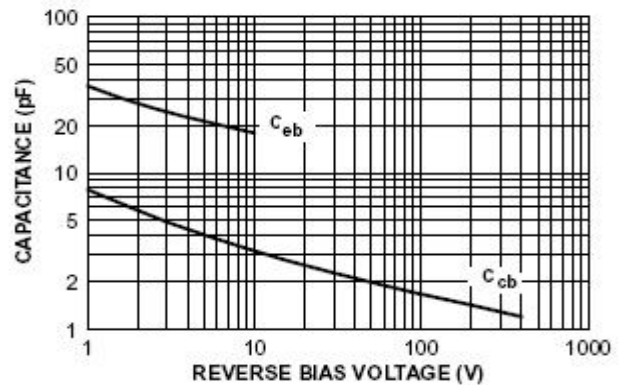
Base-Emitter ON Voltage vs Collector Current



Collector-Cutoff Current vs Ambient Temperature



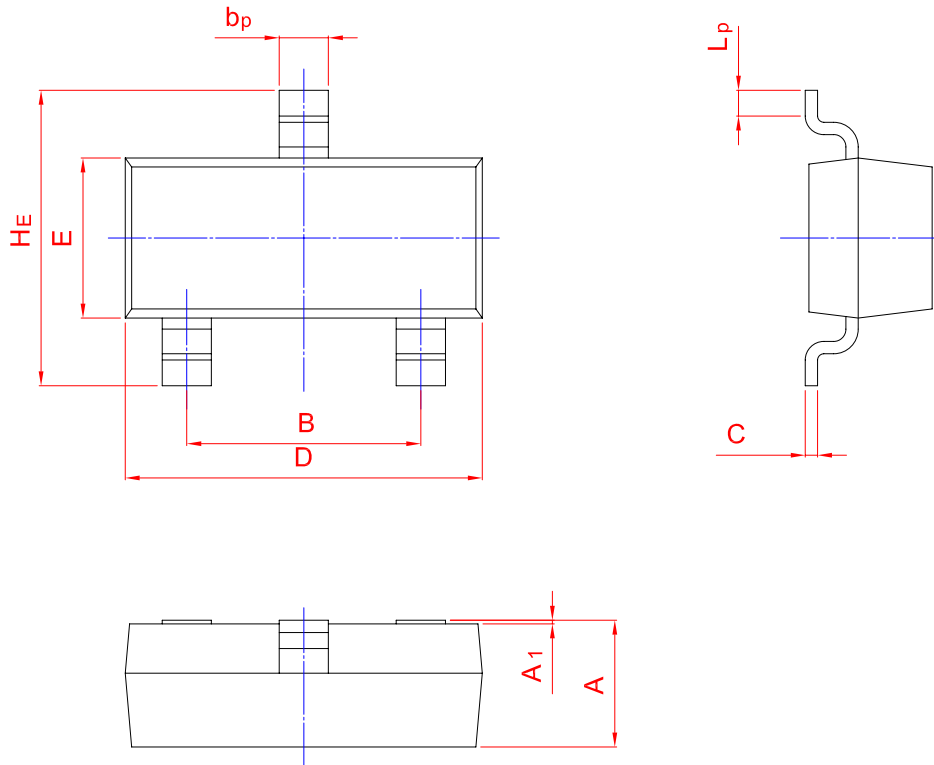
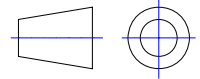
Collector-Base and Emitter-Base Capacitance vs Reverse Bias Voltage



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

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UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20